TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

TPCP8004

Notebook PC Applications

Portable Equipment Applications

- Small footprint due to a small and thin package
- · High speed switching
- Small gate charge: Qg = 26nC (typ.)
- Low drain-source ON-resistance: $RDS(ON) = 7m\Omega(typ.)$
- High forward transfer admittance: $|Y_{fs}| = 21S$ (typ.)
- Low leakage current: $I_{DSS} = 10\mu A \text{ (max) (V}_{DS} = 30V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5V ($V_{DS} = 10V$, $I_{D} = 1$ mA)

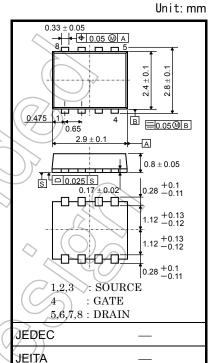
Absolute Maximum Ratings (Ta=25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	30	V
Drain-gate voltage (R _{GS} =20 kΩ)		V_{DGR}	30	V
Gate-source voltage		V _{GSS} <	±20	У
Drain current	DC (Note 1)	ID	8.3	
	Pulse (Note 1)	IDP	33.2	A
Drain power dissipation (t = 5 s) (Note 2a)		PD	1.68	W
Drain power dissipa	PD	0.84	W	
Single-pulse avalan	Eas	17,9	mJ	
Avalanche current		I _{AR}	8.3	Α
Repetitive avalanche energy (Note 4)		E _{AR}	0.021	mJ
Channel temperature		Tch	150	°C
Storage temperature range		T _{stg}	-55 to 150	°C

Note: For Notes 1 to 5, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

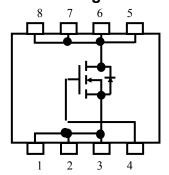


Weight: 0.017g(typ.)

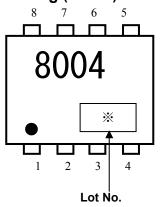
TOSHIBA

Circuit Configuration

2-3V1K



Marking (Note 5)



Start of commercial production 2007-07

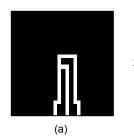
Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	R _{th (ch-a)}	74.4	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	R _{th (ch-a)}	148.8	°C/W

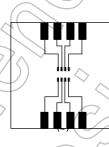
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



FR-4 $25.4\times25.4\times0.8$ (Unit: mm)



FR-4 $25.4 \times 25.4 \times 0.8$ (Unit: mm)

Note 3: V_{DD} =24V, T_{ch} = 25°C (initial), L =0.2mH, R_G = 1 Ω , I_{AR} =8.3 A

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

Weekly code: (Three digits)



Week of manufacture

(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture

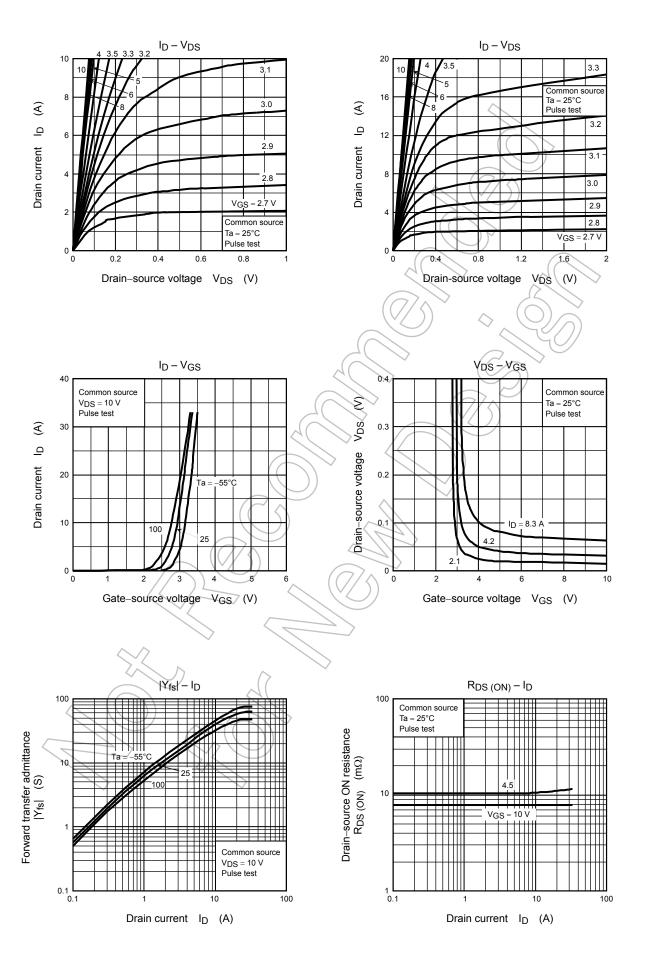
(The last digit of the year)

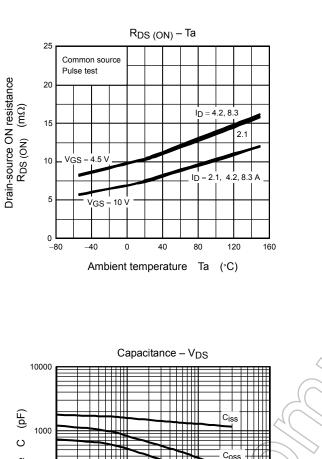
Electrical Characteristics (Ta = 25°C)

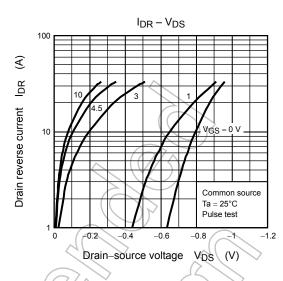
Cha	racteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	rrent	IGSS	$V_{GS}=\pm 20~V,~V_{DS}=0~V$	_	_	±100	nA	
Drain cutoff curr	ent	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_	V	
Gate threshold v	oltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1\text{mA}$	1.3	4	2.5	V	
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = 4.5 V, I _D = 4.2A		10.5	14	- mΩ	
			V _{GS} = 10 V, I _D = 4.2A	/A	7	8.5		
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 4.2A		21	_	S	
Input capacitance Reverse transfer capacitance		C _{iss}	V _{DS} =10 V, V _{GS} =0 V,	> —	1270	_	pF	
		C _{rss}		_	240	_		
Output capacitance		Coss	I - IIVII IZ	_	380	/	7 I	
Switching time	Rise time	t _r	V _{GS} 10 V I _D = 4.2A C C V _{OUT}	-6	12	> -	ns	
	Turn-on time	t _{on}		7	23) —		
	Fall time	t _f	2.5.4.4.4.2.5.4.5.4.5.5.5.5.5.5.5.5.5.5.	7	9	_		
	Turn-off time	t _{off}	V _{DD} ≈ 15 V Duty ≤ 1%, t _W = 10 μs		35	_		
Total gate charge		Qg		_	26			
(gate-source plus gate-drain)		39	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V},$		20		nC	
Gate-source cha	arge 1	Q _{gs1}	I _D =8.3 A	_	3.8	_		
Gate-drain ("Mill	er") charge	Qgd			8	_		

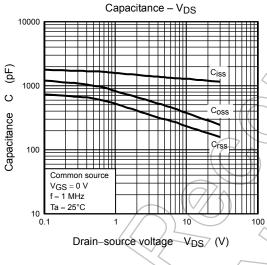
Source-Drain Ratings and Characteristics (Ta = 25°C)

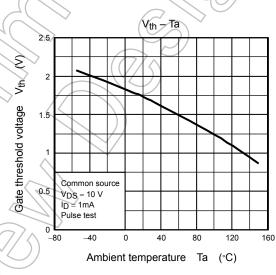
Characteristic	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP} —	_	_	33.2	Α
Forward voltage (diode)	V_{DSF} $I_{DR} = 8.3 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.2	V

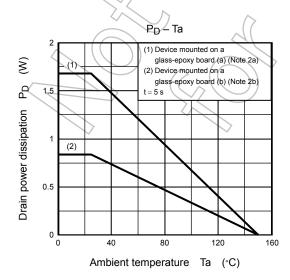


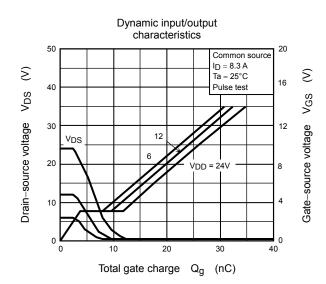


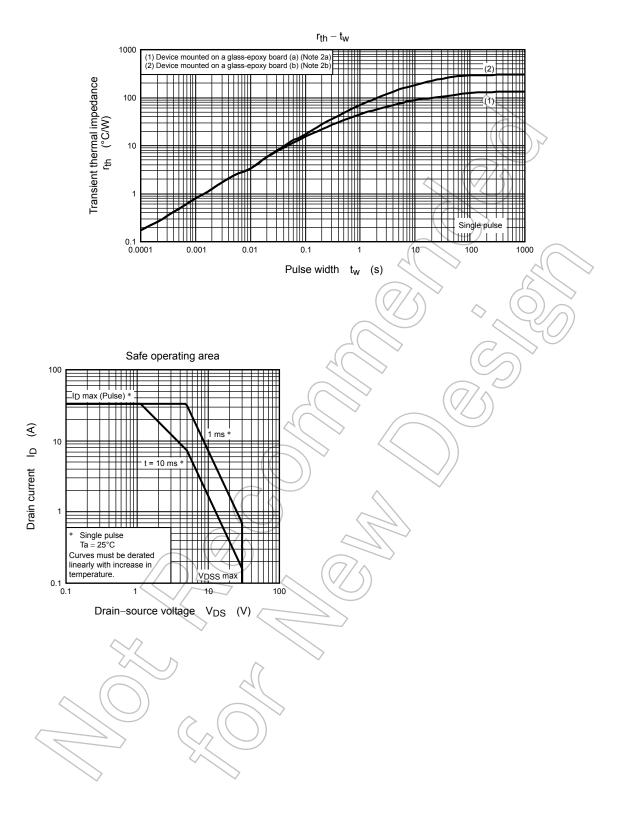












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